

2SC3551

FUJI POWER TRANSISTOR

TRIPLE DIFFUSED PLANER TYPE
HIGH VOLTAGE,HIGH SPEED SWITCHING

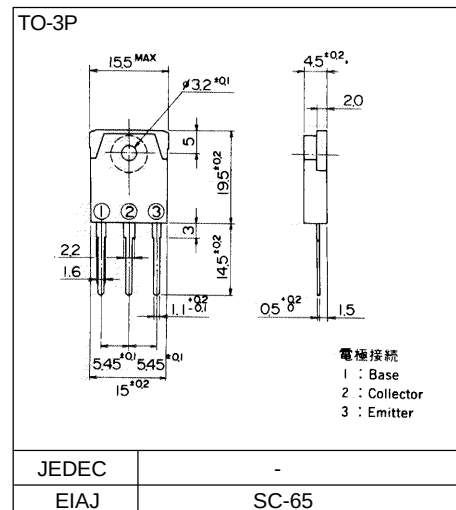
Features

- High voltage,High speed switching
- High reliability

Applications

- Switching regulators
- Ultrasonic generators
- High frequency inverters
- General purpose power amplifiers

Outline Drawings



Maximum ratings and characteristics

Absolute maximum ratings (T_c=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit
Collector-Base voltage	V _{CB0}	900	V
Collector-Emitter voltage	V _{CE0}	800	V
Collector-Emitter voltage	V _{CE0(SUS)}	-	V
Emitter-Base voltage	V _{EB0}	10	V
Collector current	I _C	5	A
Base current	I _B	3	A
Collector power dissipation	P _C	80	W
Operating junction temperature	T _j	+150	°C
Storage temperature	T _{stg}	-55 to +150	°C

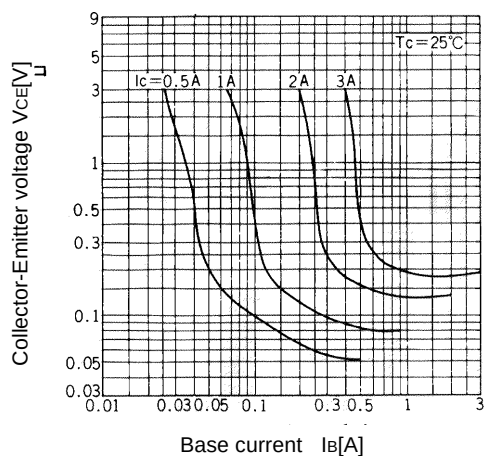
Electrical characteristics (T_c =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Base voltage	V _{CB0}	I _{CBO} = 1mA	900			V
Collector-Emitter voltage	V _{CE0}	I _{CE0} = 10mA	800			V
Collector-Emitter voltage	V _{CE0(SUS)}		-	-		V
Emitter-Base voltage	V _{EB0}	I _{EB0} = 1mA	10	-		V
Collector-Base leakage current	I _{CBO}	V _{CB0} = 900V		-	1.0	mA
Emitter-Base leakage current	I _{EB0}	V _{EB0} = 10V		-	1.0	mA
D.C. current gain	h _{FE}	I _C = 2A, V _{CE} = 5V	10			
Collector-Emitter saturation voltage	V _{CE(Sat)}	I _C = 2A, I _B = 0.4A			1.0	V
Base-Emitter saturation voltage	V _{BE(Sat)}				1.5	V
*1	t _{on}	I _C = 3A, I _{B1} = 0.6A			1.0	μs
Switching time	t _{stg}	I _{B2} = -1.2A, R _L = 100 ohm			4.0	μs
	t _f	P _w = 20 μs Duty=<2%			0.8	μs

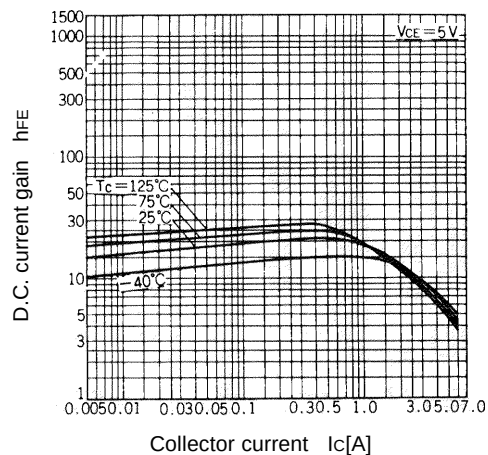
Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(j-c)}	Junction to case			1.5	°C/W

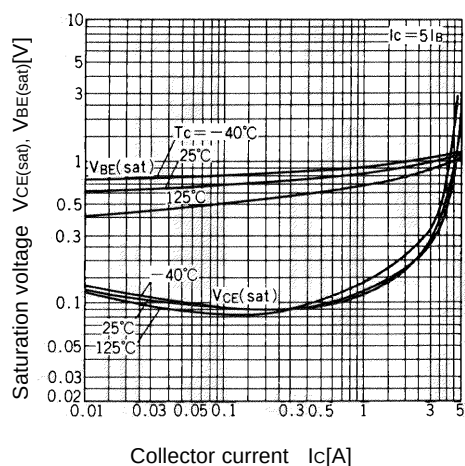
Characteristics



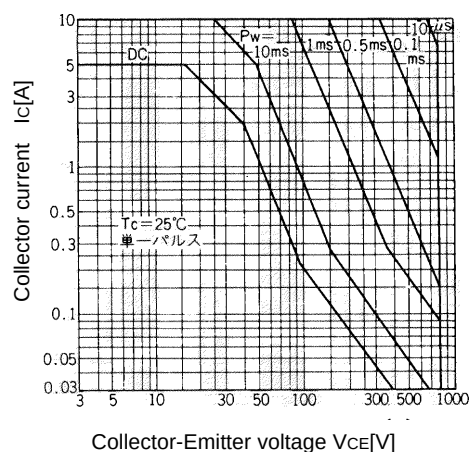
Collector Output Characteristics



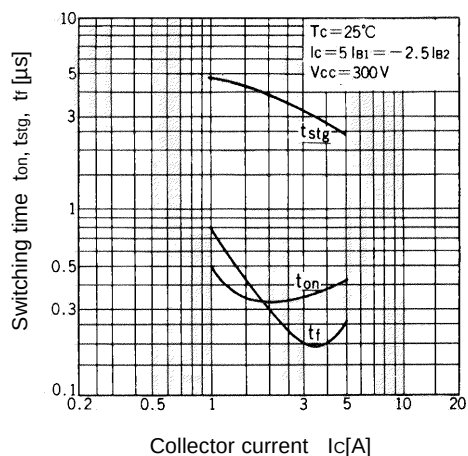
DC Current Gain



Base and Collector Saturation Voltage



Safe Operating Area



Switching Time

*1 Switching Time Test Circuit

